

MPS8050



NPN General Purpose Amplifier

This device is designed for general purpose audio amplifier applications at collector currents to 500 mA. Sourced from Process 30.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	25	V
V _{CBO}	Collector-Base Voltage	40	V
V _{EBO}	Emitter-Base Voltage	6.0	V
I _C	Collector Current - Continuous	1.0	A
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		MPS8050	
P _D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{ heta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

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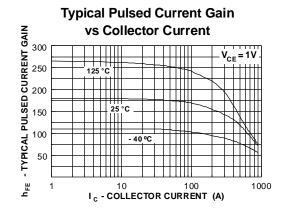
Electrical	Chara	otorictics
Electrical	Ullala	ししせいろいしょ

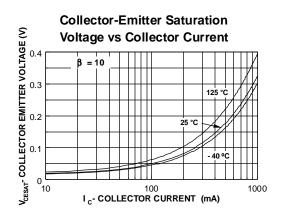
TA = 25°C unless otherwise noted

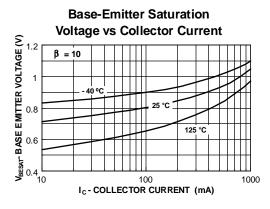
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Sustaining Voltage*	$I_{\rm C} = 30 \text{ mA}, I_{\rm B} = 0$	25		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	40		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	6.0		V
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 35 \text{ V}, I_{E} = 0$		0.1	μΑ
I _{CES}	Collector-Cutoff Current	$V_{CE} = 20 \text{ V}, I_{E} = 0$		75	nA
ON CHAR	RACTERISTICS	$I_C = 5.0 \text{ mA}, V_{CF} = 1.0$	45	<u> </u>	1
· TE	20 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0	$I_C = 0.0 \text{ m/s}, V_{CE} = 1.0$ $I_C = 100 \text{ mA}, V_{CE} = 1.0$ $I_C = 800 \text{ mA}, V_{CE} = 1.0$	80 40	300	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 800 mA, I _B = 80 mA		0.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 800 \text{ mA}, I_B = 80 \text{ mA}$		1.2	V

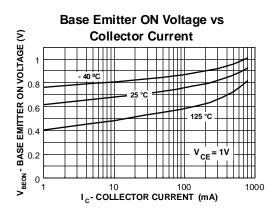
^{*}Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 1.0%

Typical Characteristics





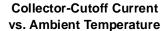


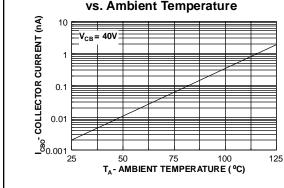


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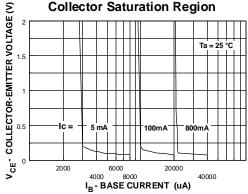
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Typical Characteristics (continued)

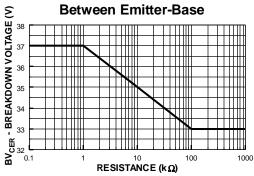




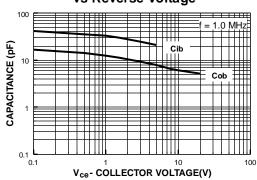
Collector Saturation Region



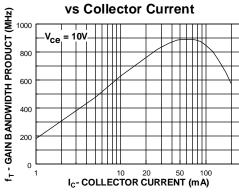
Collector-Emitter Breakdown Voltage with Resistance



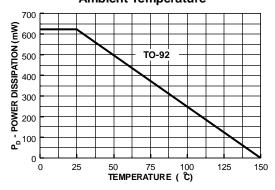
Input and Output Capacitance vs Reverse Voltage



Gain Bandwidth Product



Power Dissipation vs Ambient Temperature



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